

CY7C1041CV33 Automotive

4-Mbit (256 K × 16) Static RAM

Features

- Temperature ranges
 Automotive-A: -40 °C to 85 °C
 Automotive-E: -40 °C to 125 °C
- Pin and function compatible with CY7C1041BNV33
- High speed
 □ t_{AA} = 10 ns (Automotive-A)
 □ t_{AA} = 12 ns (Automotive-E)
- Low active power □ 432 mW (max)
- 2.0 V data retention
- Automatic power down when deselected
- TTL-compatible inputs and outputs
- Easy memory expansion with CE and OE features
- Available in Pb-free and non Pb-free 44-pin 400 Mil SOJ, 44-pin TSOP II and 48-ball FBGA packages

Functional Description

The CY7C1041CV33 Automotive is a high performance CMOS static RAM organized as 262,144 words by 16 bits.

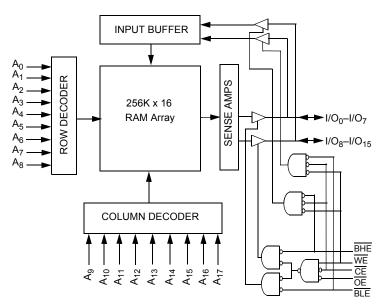
To write to the device, take Chip Enable (CE) and Write Enable (WE) inputs LOW. If Byte Low Enable (BLE) is LOW, then data from I/O pins (I/O₀ through I/O₇), is written into the location specified on the address pins (A₀ through A₁₇). If Byte High Enable (BHE) is LOW, then data from I/O pins (I/O₈ through I/O₁₅) is written into the location specified on the address pins (A₀ through A₁₇).

To read <u>from</u> the device, take Chip Enable ($\overline{\text{CE}}$) and Output Enable ($\overline{\text{OE}}$) LOW while forcing the Write Enable (WE) HIGH. If Byte Low Enable (BLE) is LOW, then data from the memory location specified by the address pins appear on I/O₀ to I/O₇. If Byte High Enable (BHE) is LOW, then data from memory appears on I/O₈ to I/O₁₅. For more information, see the Truth Table on page 10 for a complete description of Read and Write modes.

The input and output pins (I/O_0 through I/O_{15}) are placed in a high impedance state when <u>the</u> device is deselected (\overline{CE} HIGH), the outputs are disabled (\overline{OE} HIGH), the BHE and <u>BLE</u> are disabled (BHE, BLE HIGH), or during a write operation (\overline{CE} LOW and WE LOW).

For best practice recommendations, refer to the Cypress application note AN1064, SRAM System Guidelines.

Logic Block Diagram



Cypress Semiconductor Corporation Document Number: 001-67307 Rev. ** San Jose, CA 95134-1709 • 408-943-2600 Revised March 11, 2011



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Selection Guide

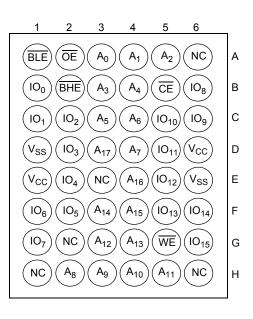
Description		-10	-12	-20	Unit
Maximum Access Time		10	12	20	ns
Maximum Operating Current	Automotive-A	100	-	85	mA
	Automotive-E	-	120	90	mA
Maximum CMOS Standby Current	Automotive-A	10	-	10	mA
	Automotive-E	-	15	15	mA

Pin Configuration

Figure 1. 44-pin SOJ/TSOP II (Top View) ^[1]

A ₀ [0	44		A ₁₇
	2	43	F	A ₁₆
A ₂		42	F	A ₁₅
	4		E	OE
	-	41		
A ₄		40	E	BHE
CEL	6	39		BLE
	7	38		IO ₁₅
	8	37		10 ₁₄
10 ₂ [9	36		IO ₁₃
	10	35		IO ₁₂
V _{CC} [11	34		V _{SS}
V _{SS} [12	33		V _{CC}
IO ₄	13	32	F	IO ₁₁
	14	31	F	IO ₁₀
	15	30	F	IO ₉
107	16	29	F	10 ₈
	17	28	F	NC
	18	27	F	A ₁₄
A ₆	19	26	F	A ₁₄ A ₁₃
A7	20	25	F	A ₁₃ A ₁₂
A ₈	21	23	Ħ	
	22		Ħ	A ₁₁
A ₉ [- 22	23	μ	A ₁₀

Figure 2. 48-ball FBGA Pinout (Top View) ^[1]





Pin Definitions

Pin Name	SOJ, TSOP Pin Number	BGA Pin Number	I/О Туре	Description
A ₀ -A ₁₇	1–5, 18–27, 42–44	A3, A4, A5, B3, B4, C3, C4, D4, H2, H3, H4, H5, G3, G4, F3, F4, E4, D3	Input	Address Inputs. Used to select one of the address locations.
I/O ₀ –I/O ₁₅	7–10,13–16, 29–32, 35–38	B1, C1, C2, D2, E2, F2, F1, G1, B6, C6, C5, D5, E5, F5, F6, G6	Input or Output	Bidirectional Data I/O lines. Used as input or output lines depending on operation.
NC	28	A6, E3, G2, H1, H6	No Connect	No Connects. Not connected to the die.
WE	17	G5	Input or Control	Write Enable Input, Active LOW. When selected LOW, a write is conducted. When deselected HIGH, a read is conducted.
CE	6	B5	Input or Control	Chip Enable Input, Active LOW. When LOW, selects the chip. When HIGH, deselects the chip.
BHE, BLE	40, 39	B2, A1	Input or Control	<u>Byte</u> Write Select Inputs, Active LOW . BHE controls $I/O_{15} - I/O_8$, BLE controls $I/O_7 - I/O_0$.
ŌĒ	41	A2	Input or Control	Output Enable, Active LOW . Controls the direction of the I/O pins. When LOW, the I/O pins are allowed to behave as outputs. When deasserted HIGH, the I/O pins are tri-stated and act as input data pins.
V _{SS}	12, 34	D1, E6	Ground	Ground for the Device. Connected to ground of the system.
V _{CC}	11, 33	D6, E1	Power Supply	Power Supply Inputs to the Device.



CY7C1041CV33 Automotive

Maximum Ratings

Exceeding maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage Temperature65 °C to +150 °C
Ambient Temperature with Power Applied
Supply Voltage on V_{CC} Relative to $GND^{[2]}$ –0.5 V to +4.6 V
DC Voltage Applied to Outputs in High Z State ^[2] –0.5 V to V_{CC} + 0.5 V
in High Z State ^[2] –0.5 V to V _{CC} + 0.5 V
DC Input Voltage ^[2] –0.5 V to V _{CC} + 0.5 V

Current into Outputs (LOW)	20 mA
Static Discharge Voltage> (MIL-STD-883, Method 3015)	> 2001 V
Latch Up Current>	200 mA

Operating Range

Range	Ambient Temperature (T _A)	V _{cc}
Automotive-A	–40 °C to +85 °C	$3.3~V\pm10\%$
Automotive-E	–40 °C to +125 °C	

Electrical Characteristics

Over the Operating Range

Parameter	Description Test Conditions			-1	10	-12		-20		Unit
Falameter	Description	Test condition			Max	Min	Max	Min	Max	Onit
V _{OH}	Output HIGH Voltage	V _{CC} = Min, I _{OH} = -4.0 m	۱A	2.4	_	2.4	—	2.4	-	V
V _{OL}	Output LOW Voltage	V _{CC} = Min, I _{OL} = 8.0 mA	١	-	0.4	-	0.4	-	0.4	V
V _{IH}	Input HIGH Voltage			2.0	V _{CC} + 0.3	2.0	V _{CC} + 0.3	2.0	V _{CC} + 0.3	V
V _{IL} ^[2]	Input LOW Voltage			-0.3	0.8	-0.3	0.8	-0.3	0.8	V
I _{IX}	Input Leakage	$GND \leq V_I \leq V_{CC}$	Auto-A	-1	+1	-	—	-1	+1	μA
	Current		Auto-E –	-	-	-20	+20	-20	+20	
I _{OZ}	Output Leakage	$GND \leq V_{OUT} \leq V_{CC}$,	Auto-A	-1	+1	-	—	-1	+1	μA
	Current	Output disabled	Auto-E	—	-	-20	+20	-20	+20	
I _{CC}	V _{CC} Operating	V _{CC} = Max,	Auto-A	-	100	-	_	-	85	mA
	Supply Current	$f = f_{MAX} = 1/t_{RC}$	Auto-E	-	-	-	120	-	90	
I _{SB1}		Max V_{CC} , $\overline{CE} \ge V_{IH}$,	Auto-A	—	40	-	—	-	40	mA
	Down Current —TTL Inputs	$V_{IN} \ge V_{IH}$, or $V_{IN} \le V_{IL}$, f = f _{MAX}	Auto-E	_	_	_	45	-	45	
I _{SB2}	Automatic CE Power		Auto-A	-	10	_	-	-	10	mA
	Down Current — CMOS Inputs	$\begin{array}{l} {\rm CE} \geq {\rm V}_{\rm CC} - 0.3 \ {\rm V}, \\ {\rm V}_{\rm IN} \geq {\rm V}_{\rm CC} - 0.3 \ {\rm V}, \\ {\rm or} \ {\rm V}_{\rm IN} \leq 0.3 \ {\rm V}, \ {\rm f} = 0 \end{array}$	Auto-E	_	-	-	15	_	15	



Capacitance

Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Test Conditions	Мах	Unit
C _{IN}	Input Capacitance	$T_A = 25 \text{ °C}, f = 1 \text{ MHz}, V_{CC} = 3.3 \text{ V}$	8	pF
C _{OUT}	Output Capacitance		8	pF

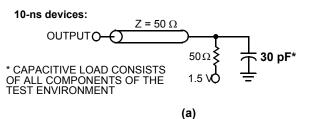
Thermal Resistance

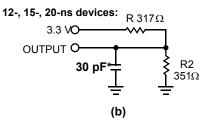
Tested initially and after any design or process changes that may affect these parameters.

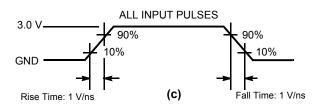
Parameter	Description	Test Conditions	SOJ	TSOP II	FBGA	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Test conditions follow standard test methods and procedures for measuring	25.99	42.96	38.15	°C/W
Θ ^{JC}	Thermal Resistance (Junction to Case)	thermal impedance, per EIA/JESD51	18.8	10.75	9.15	°C/W

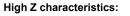
AC Test Loads and Waveforms

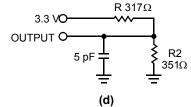
Figure 3. AC Test Loads and Waveforms ^[3]











Note

3. AC characteristics (except High Z) for 10 ns parts are tested using the load conditions shown in Figure 3 (a). All other speeds are tested using the Thevenin load shown in Figure 3 (b). High Z characteristics are tested for all speeds using the test load shown in Figure 3 (d).



Switching Characteristics

Over the Operating Range ^[4]

Demonster	Description	_	-	10	-12		-20		Unit
Parameter	Description	1	Min	Max	Min	Max	Min	Max	Unit
Read Cycle			-						
t _{power} ^[5]	V_{CC} (Typical) to the First Access		100	-	100	-	100	-	μS
t _{RC}	Read Cycle Time		10	-	12	-	20	-	ns
t _{AA}	ddress to Data Valid		-	10	-	12	-	20	ns
t _{OHA}	Data Hold from Address Change		3	-	3	-	3	-	ns
t _{ACE}	CE LOW to Data Valid		-	10	-	12	-	20	ns
t _{DOE}	OE LOW to Data Valid	Auto-A	-	5	-	6	-	8	ns
		Auto-E	-	-	-	7	-	8	
t _{LZOE}	OE LOW to Low Z ^[6]		0	-	0	-	0	-	ns
t _{HZOE}	OE HIGH to High Z ^[6, 7]		-	5	-	6	-	8	ns
t _{LZCE}	CE LOW to Low Z ^[6]		3	-	3	-	3	-	ns
t _{HZCE}	CE HIGH to High Z ^[6, 7]		-	5	-	6	-	8	ns
t _{PU}	CE LOW to Power Up		0	-	0	-	0	-	ns
t _{PD}	CE HIGH to Power Down		-	10	-	12	-	20	ns
t _{DBE}	Byte Enable to Data Valid	Auto-A	-	5	-	6	-	8	ns
		Auto-E	-	-	_	7	-	8	
t _{LZBE}	Byte Enable to Low Z		0	-	0	-	0	-	ns
t _{HZBE}	Byte Disable to High Z		-	6	-	6	-	8	ns
Write Cycle ^{[8,}	9]								
t _{WC}	Write Cycle Time		10	-	12	-	20	-	ns
t _{SCE}	CE LOW to Write End		7	-	8	-	10	-	ns
t _{AW}	Address Setup to Write End		7	-	8	-	10	-	ns
t _{HA}	Address Hold from Write End		0	-	0	-	0	-	ns
t _{SA}	Address Setup to Write Start		0	-	0	-	0	-	ns
t _{PWE}	WE Pulse Width		7	-	8	-	10	-	ns
t _{SD}	Data Setup to Write End		5	-	6	-	8	-	ns
t _{HD}	Data Hold from Write End		0	-	0	-	0	-	ns
t _{LZWE}	WE HIGH to Low Z ^[6]		3	-	3	-	3	-	ns
t _{HZWE}	WE LOW to High Z ^[6, 7]		-	5	_	6	-	8	ns
t _{BW}	Byte Enable to End of Write		7	-	8	-	10	-	ns

Notes

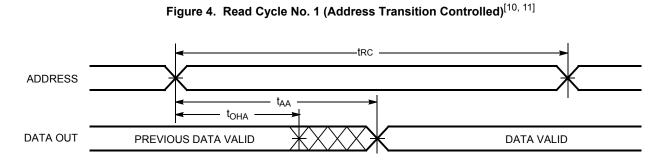
4. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, and input pulse levels of 0 to 3.0 V.

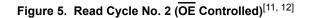
the contributions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, and input pulse levels of 0 to 3.0 V.
the power supply is at typical V_{CC} values until the first memory access is performed.
At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZDE}, t_{HZDE} is less than t_{LZDE}, and t_{HZWE} is less than t_{LZWE} for any device.
t_{HZOE}, t_{HZCE}, t_{HZBE}, and t_{HZWE} are specified with a load capacitance of 5 pF as in part (d) of Figure 3 on page 6. Transition is measured ±500 mV from steady state voltage.

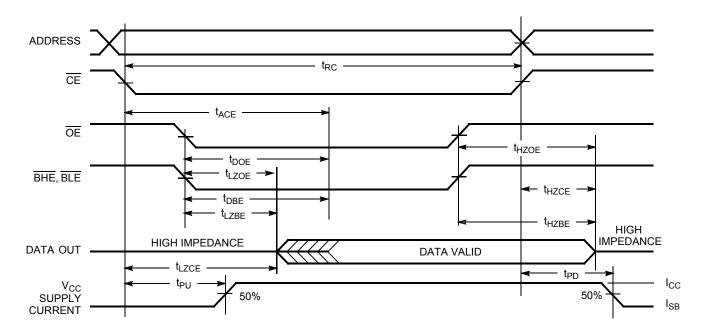
The internal write time of the memory is defined by the overlap of CE LOW, WE LOW, and BHE/BLE LOW. CE, WE, and BHE/BLE must be LOW to initiate a write. The transition of these signals terminate the write. The input data setup and hold timing is referenced to the leading edge of the signal that terminates the write.
 The minimum Write cycle time for Write Cycle No. 3 (WE controlled, OE LOW) is the sum of t_{HZWE} and t_{SD}.



Switching Waveforms







Notes

- 10. <u>Dev</u>ice is continuously selected. \overline{OE} , \overline{CE} , \overline{BHE} , and/or $\overline{BLE} = V_{IL}$.
- 11. WE is HIGH for read cycle.

^{12.} Address valid prior to or coincident with \overline{CE} transition LOW.



Switching Waveforms (continued)

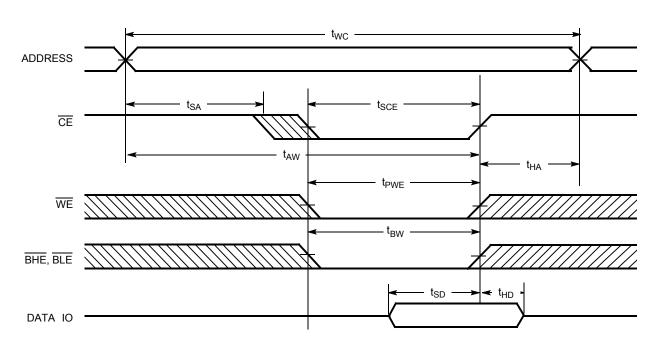
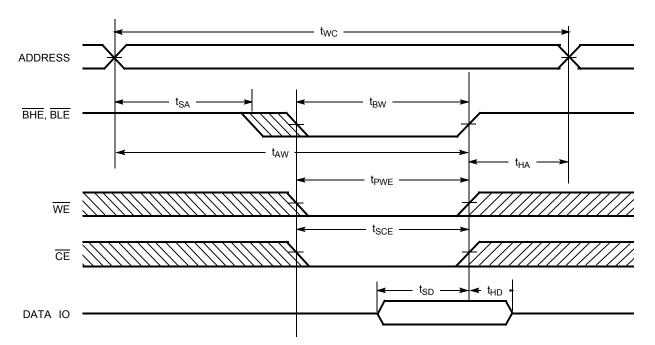


Figure 6. Write Cycle No. 1 (CE Controlled)^[13, 14]

Figure 7. Write Cycle No. 2 (BLE or BHE Controlled)



Notes

13. Data IO is high impedance if \overline{OE} , \overline{BHE} , and/or $\overline{BLE} = V_{IH}$. 14. If \overline{OE} goes HIGH simultaneously with WE going HIGH, the output remains in a high impedance state.



Switching Waveforms (continued)

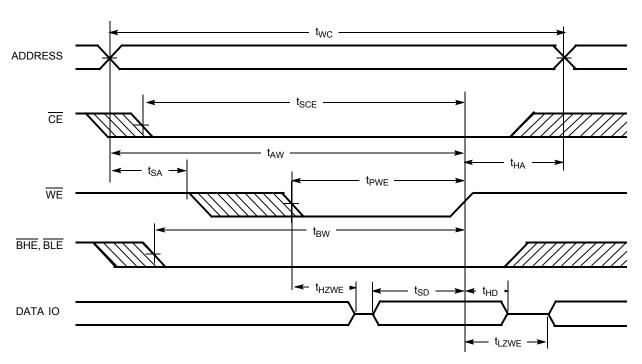


Figure 8. Write Cycle No. 3 (WE Controlled, OE LOW)

Truth Table

CE	OE	WE	BLE	BHE	I/O ₀ – I/O ₇	I/O ₈ – I/O ₁₅	Mode	Power
Н	Х	Х	Х	Х	High Z	High Z	Power Down	Standby (I _{SB})
L	L	Н	L	L	Data Out	Data Out	Read – All Bits	Active (I _{CC})
			L	Н	Data Out	High Z	Read – Lower Bits Only	Active (I _{CC})
			Н	L	High Z	Data Out	Read – Upper Bits Only	Active (I _{CC})
L	Х	L	L	L	Data In	Data In	Write – All Bits	Active (I _{CC})
			L	Н	Data In	High Z	Write – Lower Bits Only	Active (I _{CC})
			Н	L	High Z	Data In	Write – Upper Bits Only	Active (I _{CC})
L	Н	Н	Х	Х	High Z	High Z	Selected, Outputs Disabled	Active (I _{CC})
L	Х	Х	Н	Н	High Z	High Z	Selected, Outputs Disabled	Active (I _{CC})



Ordering Information

Cypress offers other versions of this type of product in many different configurations and features. The below table contains only the

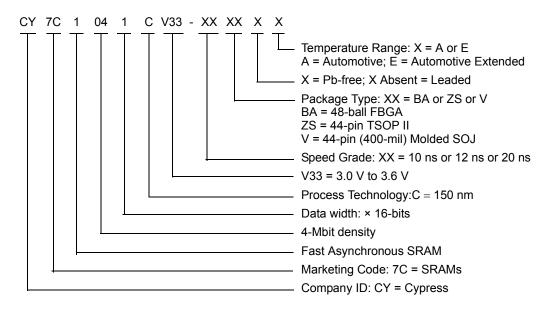
list of parts that are currently available. For a complete listing of all options, visit the Cypress website at www.cypress.com/products or contact your local sales representative.

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Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
10	CY7C1041CV33-10BAXA	51-85106	48-ball FBGA (Pb-free)	Automotive-A
	CY7C1041CV33-10ZSXA	51-85087	44-pin TSOP II (Pb-free)	
12	CY7C1041CV33-12BAXE	51-85106	48-ball FBGA (Pb-free)	Automotive-E
	CY7C1041CV33-12ZSXE	51-85087	44-pin TSOP II (Pb-free)	
20	CY7C1041CV33-20ZSXA	51-85087	44-pin TSOP II (Pb-free)	Automotive-A
	CY7C1041CV33-20VXE		44-pin (400-mil) Molded SOJ (Pb-free)	Automotive-E
	CY7C1041CV33-20ZSXE		44-pin TSOP II (Pb-free)	

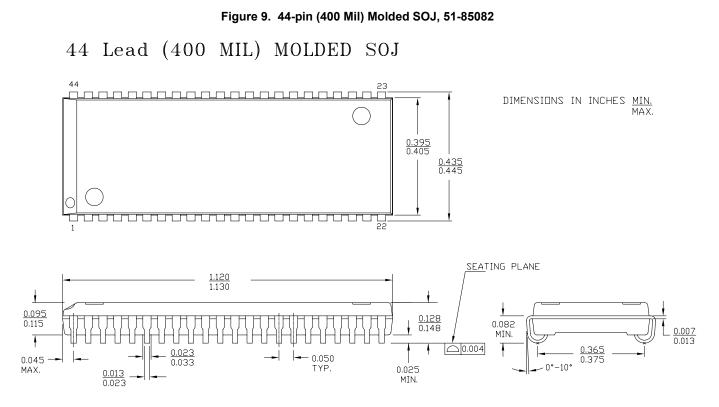
Please contact your local Cypress sales representative for availability of these parts

Ordering Code Definitions





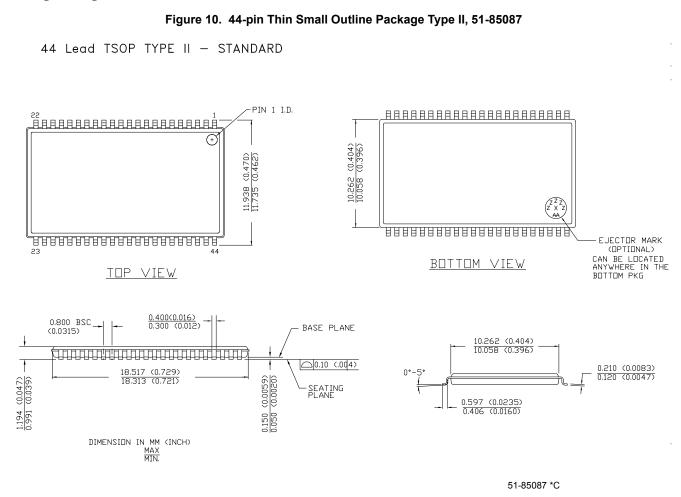
Package Diagrams



51-85082 *C



Package Diagrams (continued)





Package Diagrams (continued)

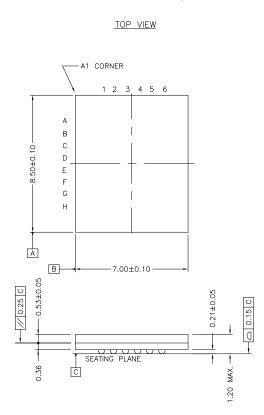
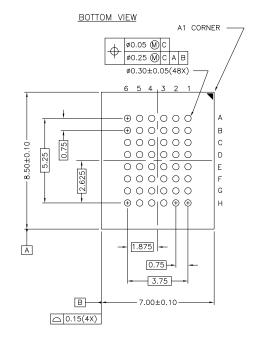


Figure 11. 48-ball FBGA (7 × 8.5 × 1.2 mm), 51-85106



51-85106 *F



Acronyms

Acronym	Description	
CE	Chip Enable	
CMOS	complementary metal oxide semiconductor	
FBGA	fine-pitch ball grid array	
I/O	input/output	
OE	Output Enable	
PLL	phase locked loop	
SOJ	Small Outline J-lead	
SRAM	static random access memory	
TSOP	thin small outline package	
TTL	transistor-transistor logic	
WE	Write Enable	

Document Conventions

Units of Measure

Symbol	Unit of Measure		
Ω	ohms		
ns	nano seconds		
V	Volts		
μs	micro seconds		
μA	micro Amperes		
mA	milli Amperes		
mm	milli meter		
ms	milli seconds		
MHz	Mega Hertz		
pF	pico Farad		
%	percent		
mW	milli Watts		
W	Watts		
°C	degree Celcius		



Document History Page

Document Title: CY7C1041CV33 Automotive, 4-Mbit (256 K × 16) Static RAM Document Number: 001-67307				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	3187164	03/03/2011		Separation of the automotive datasheet from CY7C1041CV33 spec no. 38-05134 Rev. *K. Further rev of 38-05134 would include only industrial / commercial parts.



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